

N-Channel Enhancement-Mode Vertical DMOS FETs

Features

- ▶ Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C_{iss} and fast switching speeds
- Excellent thermal stability
- Integral source-drain diode
- ► High input impedance and high gain

Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

General Description

The Supertex VN0550 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package	Wafer / Die Options						
	TO-92	NW (Die in wafer form)	NJ (Die on adhesive tape)	ND (Die in waffle pack)				
VN0550	VN0550N3-G	VN1550NW	VN1550NJ	VN1550ND				

For packaged products, -G indicates package is RoHS compliant ('Green'). Devices in Wafer / Die form are RoHS compliant ('Green'). Refer to Die Specification VF15 for layout and dimensions.

Product Summary

$BV_{DSS}\!/\!BV_{DGS}$ (V)	$R_{DS(ON)} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	I _{D(ON)} (min) (mA)
500	60	150

Absolute Maximum Ratings

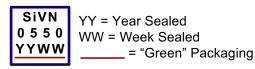
Parameter	Value
Drain-to-source voltage	BV _{DSS}
Drain-to-gate voltage	BV _{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Pin Configuration



Product Marking



Package may or may not include the following marks: Si or



Thermal Characteristics

Packag	e (c	I _D continuous) [†] (mA)	I _D (pulsed) (mA)	Power Dissipation @T _c = 25°C (W)	θ _{jc} (°C/W)	θ _{ja} (°C/W)	_{DR} † (m A)	l _{DRM} (mA)
TO-92		50	250	1.0	125	170	50	250

Notes:

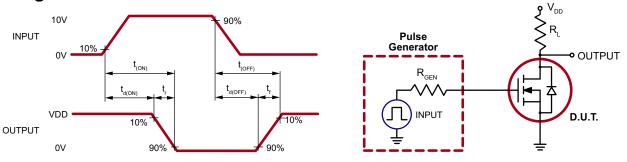
Electrical Characteristics (T_A = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions	
BV _{DSS}	Drain-to-source breakdown voltage	500	-	-	V	$V_{GS} = 0V, I_{D} = 1.0 \text{mA}$	
$V_{\rm GS(th)}$	Gate threshold voltage	2.0	-	4.0	V	$V_{GS} = V_{DS}$, $I_{D} = 1.0$ mA	
$\Delta V_{GS(th)}$	Change in V _{GS(th)} with temperature	-	-3.8	-5.0	mV/°C	$V_{GS} = V_{DS}$, $I_{D} = 1.0$ mA	
I _{GSS}	Gate body leakage current	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
		-	-	10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$	
I _{DSS}	Zero gate voltage drain current	-	-	1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$, $T_A = 125^{\circ}C$	
.		-	100	-	^	$V_{GS} = 5.0V, V_{DS} = 25V$	
D(ON)	On-state drain current	150	350	-	mA	V _{GS} = 10V, V _{DS} = 25V	
Б	Static drain-to-source on-state	-	45	-		$V_{GS} = 5.0V, I_{D} = 50mA$	
R _{DS(ON)}	resistance	-	40	60	Ω	V _{GS} = 10V, I _D = 50mA	
$\Delta R_{DS(ON)}$	Change in R _{DS(ON)} with temperature	-	1.0	1.7	%/°C	$V_{GS} = 10V, I_D = 50mA$	
G _{FS}	Forward transconductance	50	100	-	mmho	$V_{DS} = 25V, I_{D} = 50mA$	
C _{ISS}	Input capacitance	-	45	55		$V_{GS} = 0V$,	
C _{oss}	Common source output capacitance	-	8.0	10	pF	$V_{DS} = 25V$,	
C _{RSS}	Reverse transfer capacitance	-	2.0	5.0		f = 1.0MHz	
t _{d(ON)}	Turn-on time	-	-	10			
t _r	Rise time	-	-	15	ns	$V_{DD} = 25V,$	
t _{d(OFF)}	Turn-off time	-	-	10		$I_D = 150 \text{mA},$ $R_{GEN} = 25\Omega$	
t _f	Fall time	-		10		GEN	
V _{SD}	Diode forward voltage drop	-	0.8	-	V	$V_{GS} = 0V, I_{SD} = 500 \text{mA}$	
t _{rr}	Reverse recovery time	-	300	-	ns	$V_{GS} = 0V, I_{SD} = 500 \text{mA}$	

Notes:

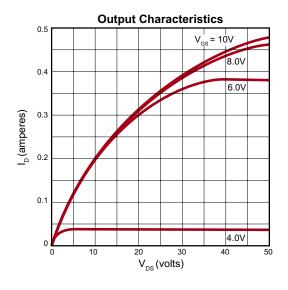
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

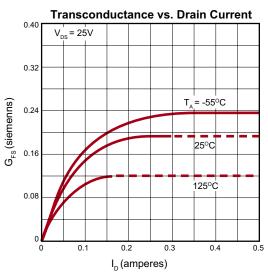
Switching Waveforms and Test Circuit

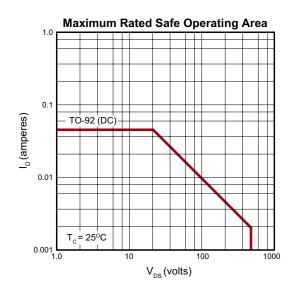


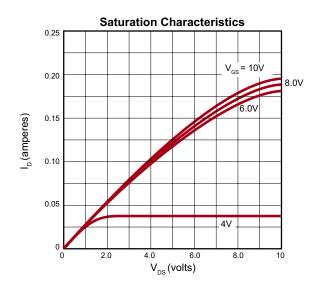
[†] I_D (continuous) is limited by max rated T_i .

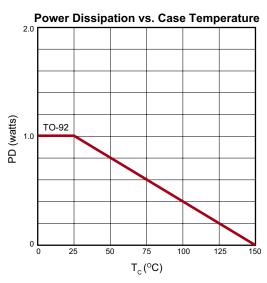
Typical Performance Curves

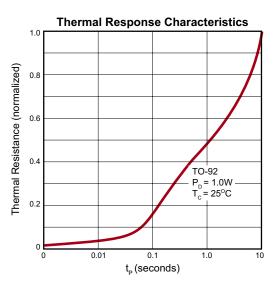




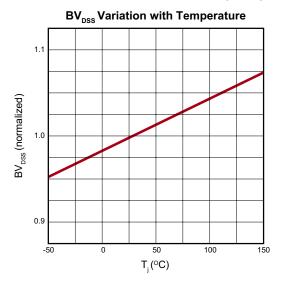


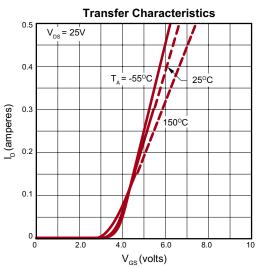


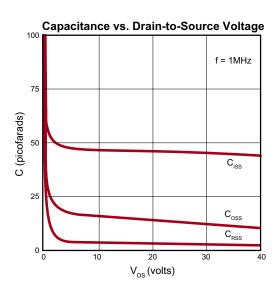


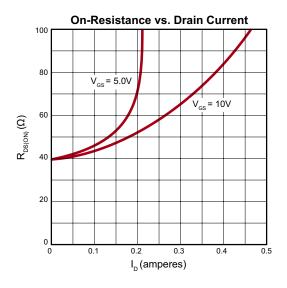


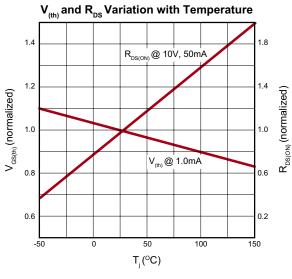
Typical Performance Curves (cont.)

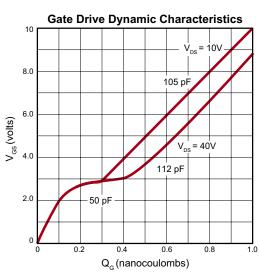




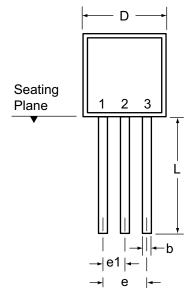


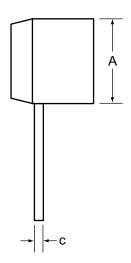






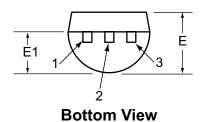
3-Lead TO-92 Package Outline (N3)





Front View

Side View



Symbol		Α	b	С	D	E	E1	е	e1	L
Dimensions (inches)	MIN	.170	.014 [†]	.014 [†]	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

Supertex inc. does not recommend the use of its products in life support applications, and will not knowingly sell them for use in such applications unless it receives an adequate "product liability indemnification insurance agreement." **Supertex inc.** does not assume responsibility for use of devices described, and limits its liability to the replacement of the devices determined defective due to workmanship. No responsibility is assumed for possible omissions and inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications refer to the **Supertex inc.** (website: http://www.supertex.com)

©2011 **Supertex inc.** All rights reserved. Unauthorized use or reproduction is prohibited.



^{*} This dimension is not specified in the JEDEC drawing.

[†] This dimension differs from the JEDEC drawing.